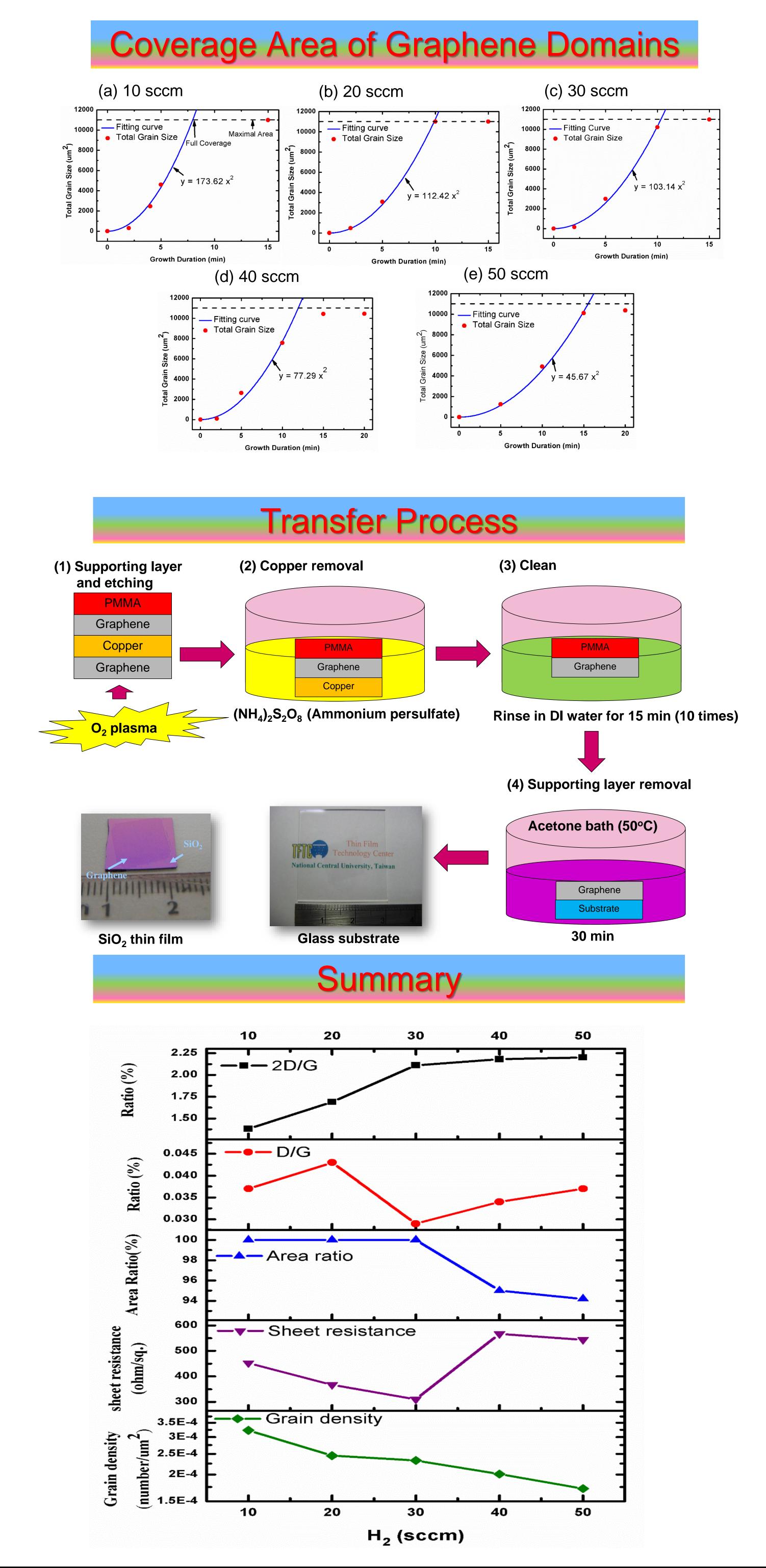


Derivation of approximately model for CVD graphene growth

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The aim in this study is controlling the nucleation density of graphene seed, furthermore, pursuing a lower sheet resistance by reducing the quantity of grain boundaries. We developed a simple derivation of approximately model for graphene growth under different hydrogen flow rate, ranging from 10 to 50 sccm. The morphology of graphene edge was become smoother with a high concentration of hydrogen flow rate. The growth parameters, CH₄ and temperature, are 0.5 sccm and 1070°C with ambient chemical vapor deposition (APCVD). The lowest sheet resistance of single layer graphene was 310 Ω/Γ and the average transmittance is 97.7 % between 350 -1000 nm wavelengths.

Coverage Area of Graphene Domains $H_2=10 \text{ sccm}$ $H_2=30 \text{ sccm}$ $H_2=50 \text{ sccm}$ **Hexagonal Domain** Copper Graphene **Dendritic Domain** Hydrogen can etch the weak C-C and the C-H bond. $Graphene + C_x H_x(s) \leftrightarrow (Graphene - C_x) + yH(s)$ Graphene H₂ flow rate **10 30 20 40 50** (sccm) **Nucleation** $3.22 \times 10^{-4} \ 2.45 \times 10^{-4} \ 2.33 \times 10^{-4} \ 2.01 \times 10^{-4} \ 1.72 \times 10^{-4}$ **Density** Copper (μm^{-2}) Carbon Growth Rate (a) (b) 30 sccm 4000 - 20 sccm Average Grain Size Average Grain Size Average Grain Size Fitting curve — Fitting curve Fitting curve **Growth Duration (min) Growth Duration (min) Growth Duration (min)** ■ Average Grain Size Average Grain Size - Fitting curve Fitting curve 4 6 8 10 12 14 16 **Growth Duration (min) Growth Duration (min)** Derivation of the Approximately model dA = LdrLet *dr=vdt* And t = growth time dA = LvdtL= circumference $L=(4\pi A)^{\frac{1}{2}}$ A= average araea $(4\pi A)^{-\frac{1}{2}}dA = vdt$ r = average radius $\frac{1}{2\pi}(4\pi A)^{\frac{1}{2}} = vt$ The average area is the second- $A = \pi(vt)^2$ order function of the growth time $A = \pi(vt)^2 = \frac{1}{2} \frac{d^2 A}{dt^2} t^2$





and growth rate of carbon atoms.

